

FDD8770/FDU8770 N-Channel PowerTrench® MOSFET

25V, 35A, 4.0mΩ



General Description

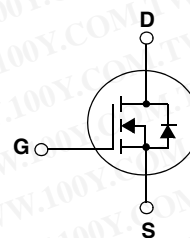
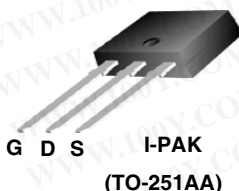
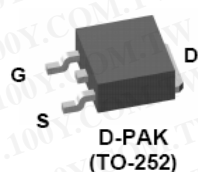
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$ and fast switching speed.

Features

- Max $r_{DS(on)}$ = 4.0mΩ at $V_{GS} = 10V$, $I_D = 35A$
- Max $r_{DS(on)}$ = 5.5mΩ at $V_{GS} = 4.5V$, $I_D = 35A$
- Low gate charge: $Q_{g(10)} = 52nC(Typ)$, $V_{GS} = 10V$
- Low gate resistance
- RoHS Compliant

Application

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|---|------------|------------|
| V_{DS} | Drain to Source Voltage | 25 | V |
| V_{GS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current -Continuous (Package Limited) | 35 | A |
| | -Continuous (Die Limited) | 210 | |
| | -Pulsed (Note 1) | 407 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 2) | 113 | mJ |
| P_D | Power Dissipation | 115 | W |
| T_J, T_{STG} | Operating and Storage Temperature | -55 to 175 | $^\circ C$ |

Thermal Characteristics

| | | | |
|-----------------|--|-----|--------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case TO-252, TO-251 | 1.3 | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient TO-252, TO-251 | 100 | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient TO-252, 1in ² copper pad area | 52 | $^\circ C/W$ |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|--------------|----------|-----------|------------|------------|
| FDD8770 | FDD8770 | TO-252AA | 13" | 12mm | 2500 units |
| FDU8770 | FDU8770 | TO-251AA | N/A(Tube) | N/A | 75 units |
| FDU8770 | FDU8770_F071 | TO-251AA | N/A(Tube) | N/A | 75 units |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------------------------------------|---|--|-----|------|-----------|----------------------|
| B_{VDSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 25 | | | V |
| $\frac{\Delta B_{VDSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, referenced to 25°C | | 13.6 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$ | | | 1 250 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |

On Characteristics

| | | | | | | |
|--|--|--|-----|------|-----|----------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ | 1.2 | 1.6 | 2.5 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, referenced to 25°C | | -5.9 | | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$ | Drain to Source On Resistance | $V_{GS} = 10\text{V}, I_D = 35\text{A}$ | | 3.3 | 4.0 | m Ω |
| | | $V_{GS} = 4.5\text{V}, I_D = 35\text{A}$ | | 4.0 | 5.5 | |
| | | $V_{GS} = 10\text{V}, I_D = 35\text{A}$ $T_J = 175^\circ\text{C}$ | | 4.8 | 5.9 | |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|-------------------|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 13\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ | | 2795 | 3720 | pF |
| C_{oss} | Output Capacitance | | | 685 | 915 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 450 | 675 | pF |
| R_g | Gate Resistance | | $f = 1\text{MHz}$ | | 1.5 | Ω |

Switching Characteristics

| | | | | | | | |
|--------------|-------------------------------|--|---|----|-----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 13\text{V}, I_D = 35\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 5\Omega$ | | 10 | 20 | ns | |
| t_r | Rise Time | | | 12 | 22 | ns | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 49 | 78 | ns | |
| t_f | Fall Time | | | 25 | 40 | ns | |
| Q_g | Total Gate Charge | | $V_{GS} = 0\text{V to } 10\text{V}$ | | 52 | 73 | nC |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{V to } 5\text{V}$ | $V_{DD} = 13\text{V}$ $I_D = 35\text{A}$ $I_g = 1.0\text{mA}$ | | 29 | 41 | nC |
| Q_{gs} | Gate to Source Gate Charge | | | | 8.1 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | | 11 | | nC |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|---------------------------------------|---|--|------|------|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{V}, I_S = 35\text{A}$ | | 0.84 | 1.25 | V |
| | | $V_{GS} = 0\text{V}, I_S = 15\text{A}$ | | 0.79 | 1.0 | |
| t_{rr} | Reverse Recovery Time | $I_F = 35\text{A}, di/dt = 100\text{A}/\mu\text{s}$ | | 32 | 48 | ns |
| Q_{rr} | Reverse Recovery Charge | $I_F = 35\text{A}, di/dt = 100\text{A}/\mu\text{s}$ | | 25 | 38 | nC |

Notes:

- 1: Pulse time < 300 μs , Duty cycle = 2%.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.3\text{mH}$, $I_{AS} = 27.5\text{A}$, $V_{DD} = 23\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

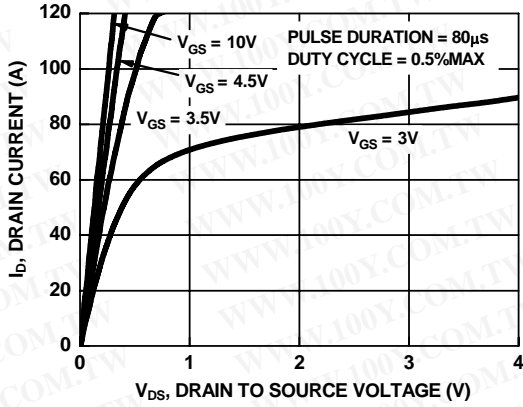


Figure 1. On Region Characteristics

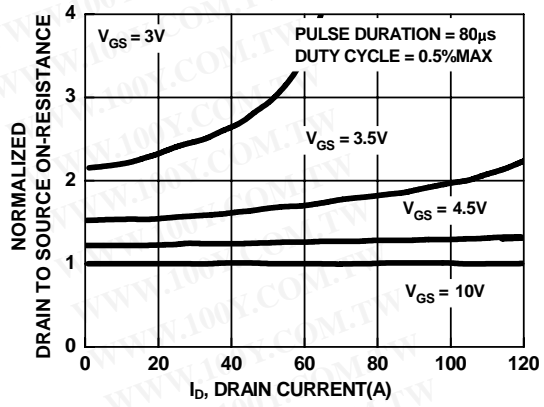


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

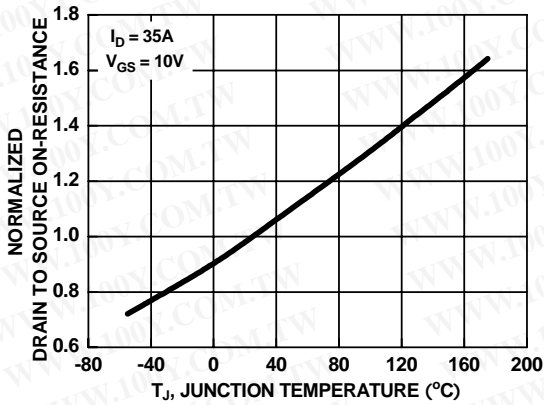


Figure 3. Normalized On Resistance vs Junction Temperature

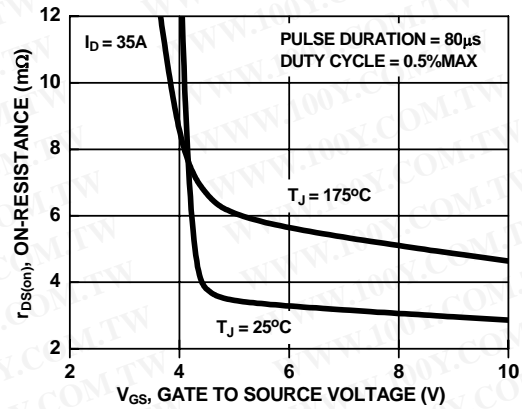


Figure 4. On-Resistance vs Gate to Source Voltage

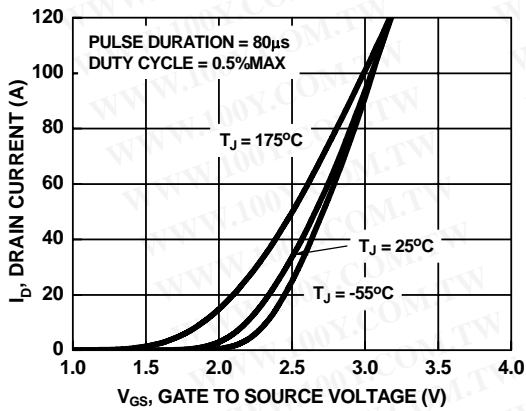


Figure 5. Transfer Characteristics

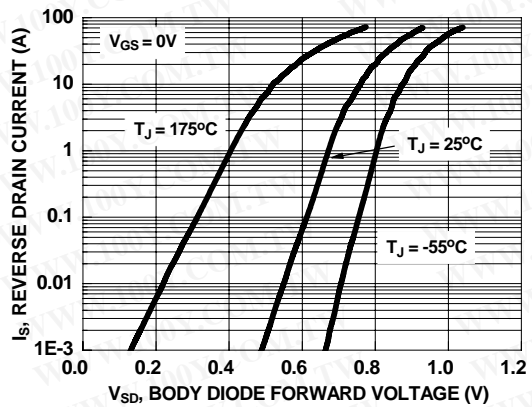


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

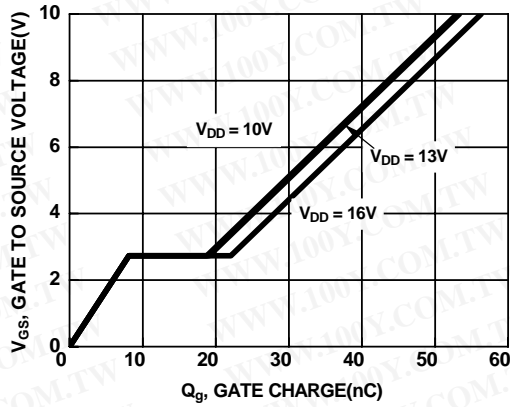


Figure 7. Gate Charge Characteristics

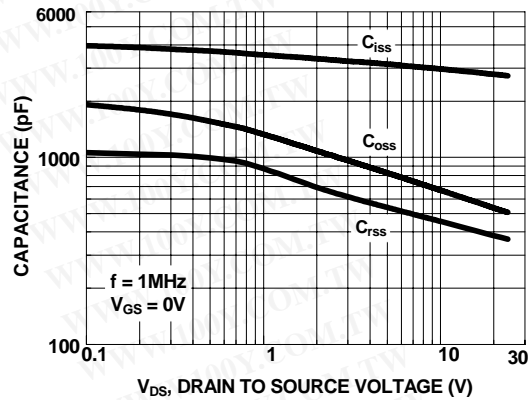


Figure 8. Capacitance vs Drain to Source Voltage

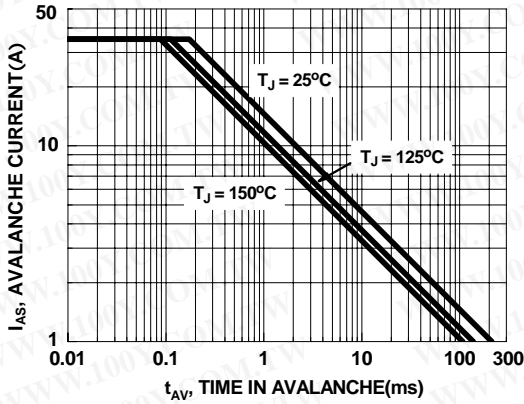


Figure 9. Unclamped Inductive Switching Capability

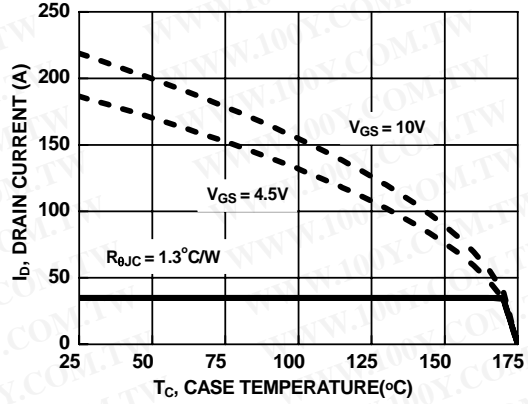


Figure 10. Maximum Continuous Drain Current vs Case Temperature

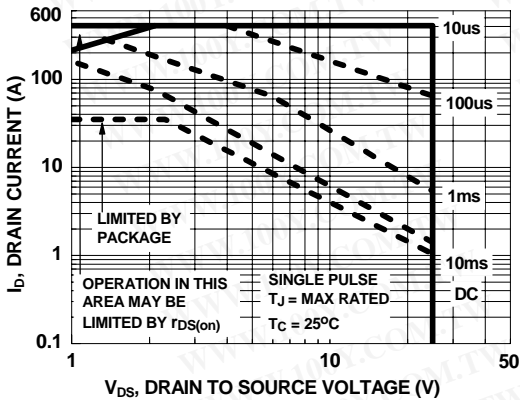


Figure 11. Forward Bias Safe Operating Area

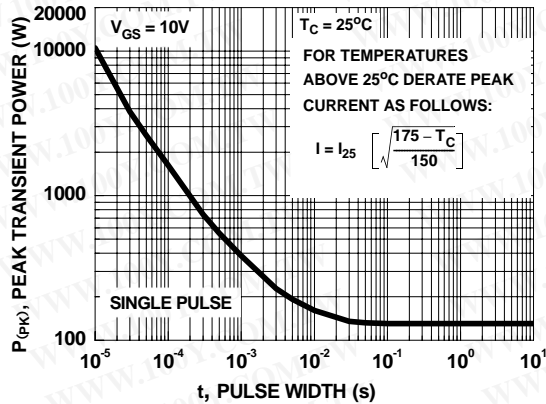


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

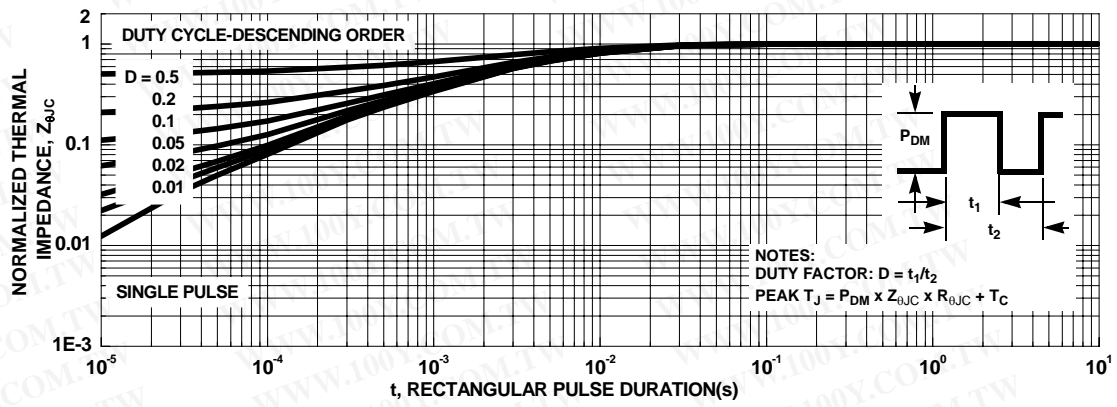


Figure 13. Transient Thermal Response Curve

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